# 2SD467

## Silicon NPN Epitaxial

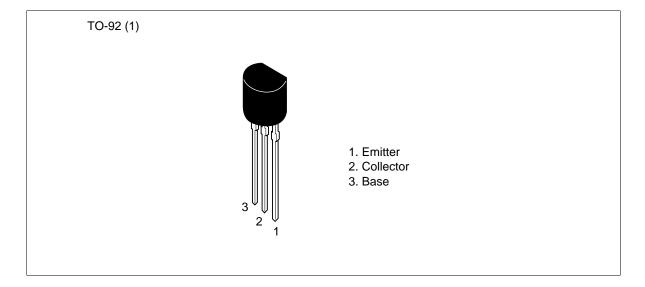
# **HITACHI**

ADE-208-1134 (Z) 1st. Edition Mar. 2001

## Application

- Low frequency power amplifier
- Complementary pair with 2SB561

#### Outline





## **2SD467**

## **Absolute Maximum Ratings** $(Ta = 25^{\circ}C)$

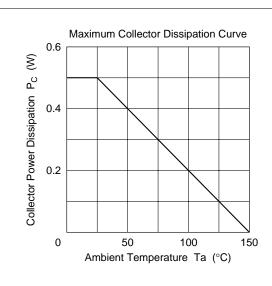
Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{\text{CBO}}$	25	V
Collector to emitter voltage	$V_{\text{CEO}}$	20	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	I <sub>c</sub>	0.7	А
Collector peak current	i <sub>C(peak)</sub>	1.0	А
Collector power dissipation	P <sub>c</sub>	0.5	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

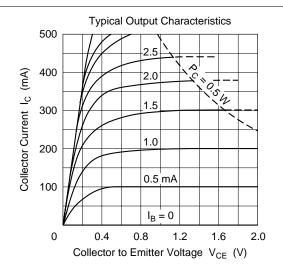
#### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

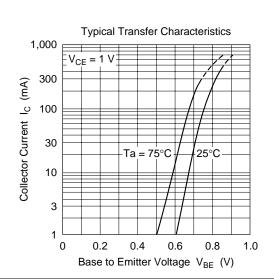
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	25	_	_	V	$I_{c} = 10 \ \mu\text{A}, \ I_{e} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	_	_	V	$I_{C} = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	1.0	μΑ	$V_{CB} = 20 \text{ V}, I_{E} = 0$
DC current transfer ratio	h <sub>FE</sub> *1	85	_	240		$V_{CE} = 1 \text{ V}, I_{C} = 0.15 \text{ A}$ (Pulse test)
Collector to emitter saturation voltage	$V_{CE(sat)}$	_	0.19	0.5	V	$I_{\rm C} = 0.5 \text{ A}, I_{\rm B} = 0.05 \text{ A}$ (Pulse test)
Base to emitter voltage	$V_{BE}$	_	0.76	1.0	V	$V_{CE} = 1 \text{ V}, I_{C} = 0.15 \text{ A}$ (Pulse test)
Gain bandwidth product	f <sub>T</sub>	_	280	_	MHz	$V_{CE} = 1 \text{ V}, I_{C} = 0.15 \text{ A}$ (Pulse test)
Collector output capacitance	Cob	_	12	_	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

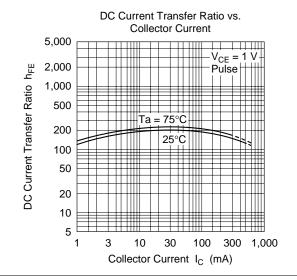
Note: 1. The 2SD467 is grouped by  $h_{\rm FE}$  as follows.

В	С
85 to170	120 to 240

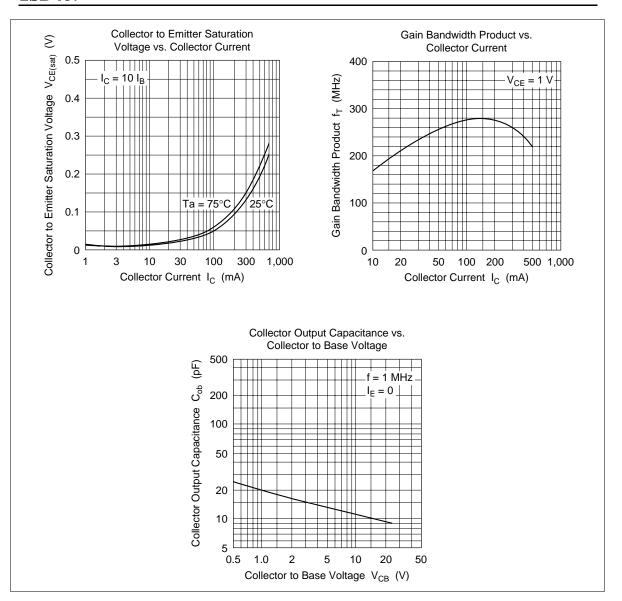




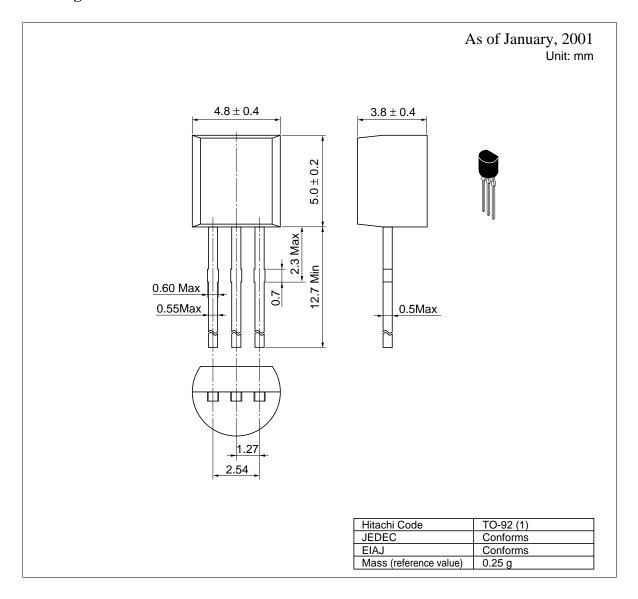




#### 2SD467



#### **Package Dimensions**



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